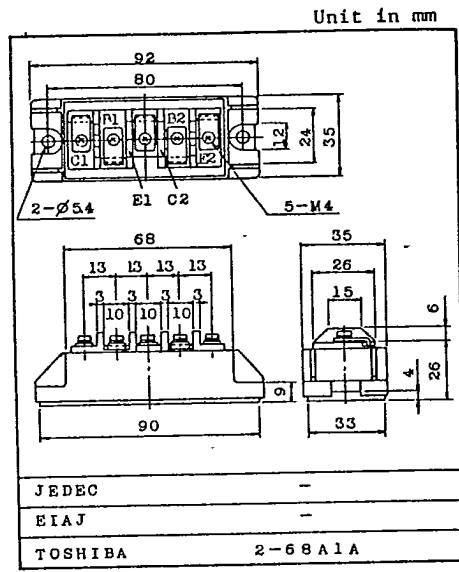
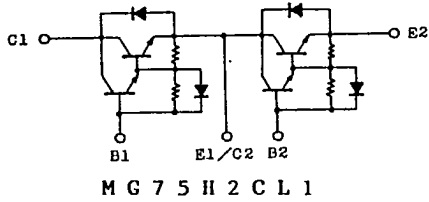


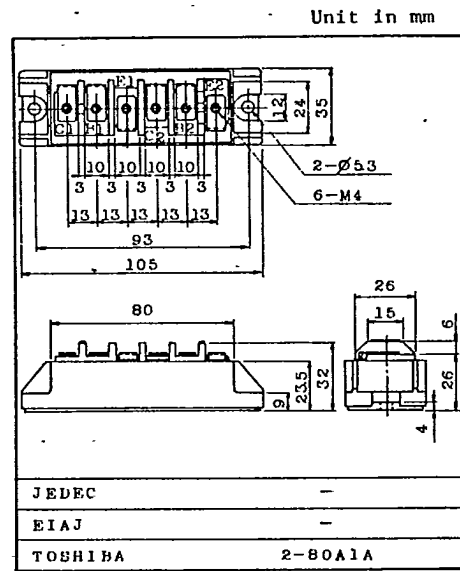
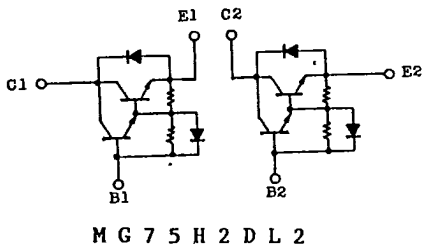


SEMICONDUCTOR
TECHNICAL DATA

MG75H2CL1
MG75H2DL2



Weight : 205g



Weight : 245g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16247

DT-33-3S



SEMICONDUCTOR

TECHNICAL DATA

MG75H2CL1

MG75H2DL2

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V _{CB0}	600	V
Collector-Emitter Sustaining Voltage		V _{CEX(SUS)}	600	V
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	500	V
Emitter-Base Voltage		V _{EBO}	6	V
Collector Current	DC	I _C	75	A
	1ms	I _{CP}	150	A
Forward Current	DC	I _F	75	A
	1ms	I _{FM}	150	A
Base Current		I _B	4	A
Collector Power Dissipation (Tc=25°C)		P _C	350	W
Junction Temperature		T _J	150	°C
Storage Temperature Range		T _{stg}	-40~125	°C
Isolation Voltage		V _{isol}	2500 (AC 1 Minute)	V
Screw Torque (Terminal/Mounting)		-	20/30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CB0}	V _{CB} =600V, I _E =0	-	-	1.0	mA
Emitter Cut-off Current		I _{EBO}	V _{EB} =6V, I _C =0	-	-	200	mA
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	I _C =0.5A, L=40mH	500	-	-	V
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =75A	80	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =75A, I _B =2A	-	-	2.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}		-	-	2.5	V
Switching Time	Turn-on Time	t _{on}	<p>50µs IB1 IB2 4µF VCC=300V</p>	-	-	2.0	µs
	Storage Time	t _{stg}		-	-	12	
	Fall Time	t _f		I _{B1} =-I _{B2} =2A DUTY CYCLE=0.5%	-	-	
Forward Voltage		V _F	I _F =75A, I _B =0	-	-	1.5	V
Reverse Recovery Time		t _{rr}	I _F =75A, V _{BE} =-3V di/dt=100A/µs	-	-	2.0	µs
Thermal Resistance		R _{th(j-c)}	Transistor	-	-	0.35	°C/W
			Diode	-	-	1.3	

TOSHIBA CORPORATION

GT1A2A

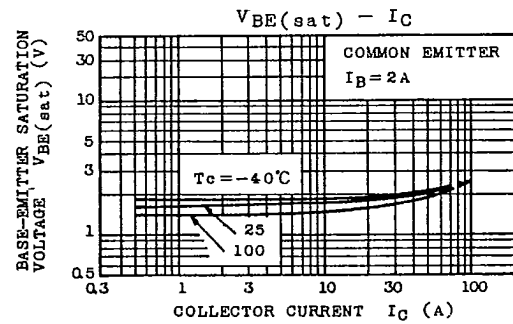
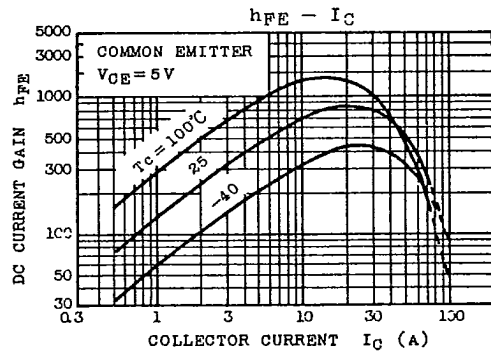
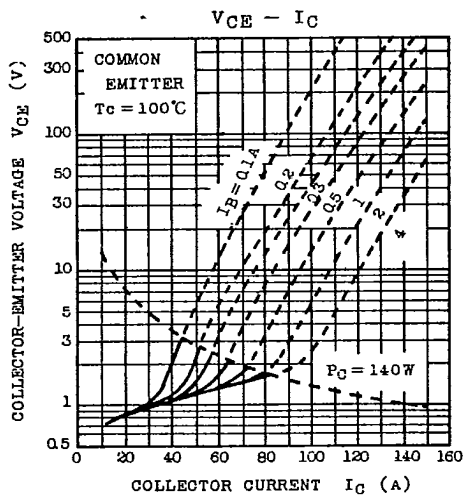
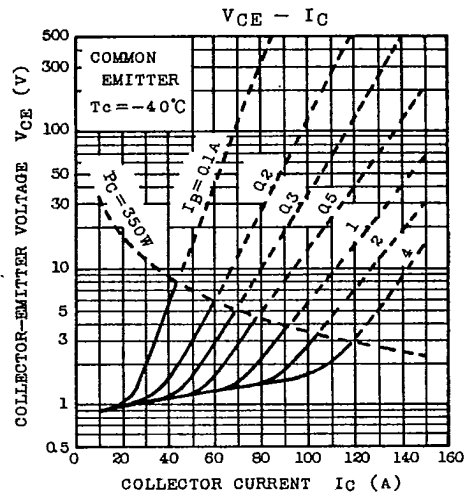
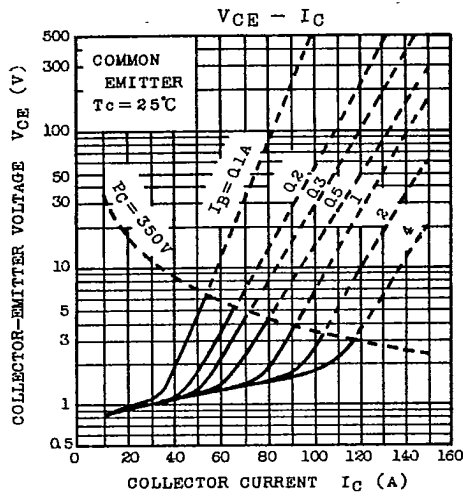


SEMICONDUCTOR

TECHNICAL DATA

MG75H2CL1

MG75H2DL2



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

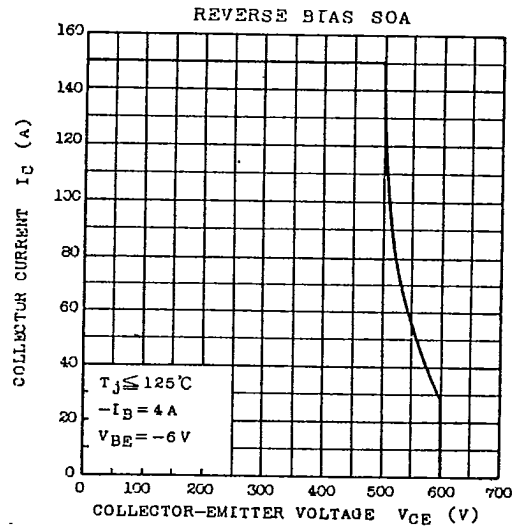
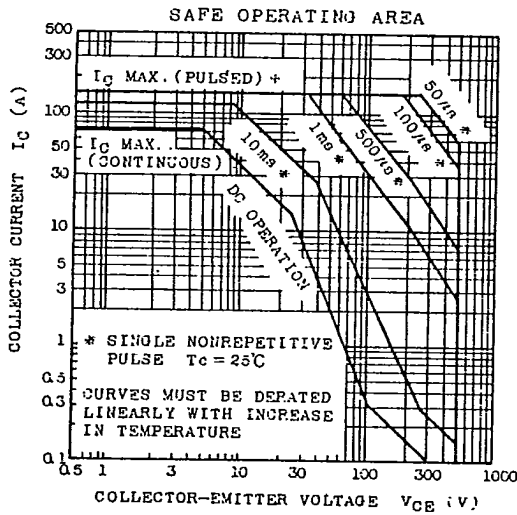
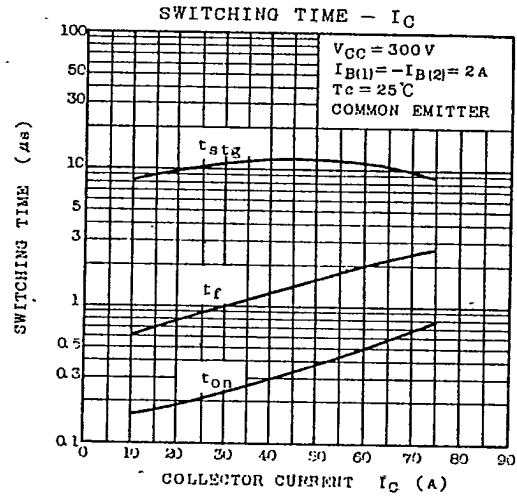
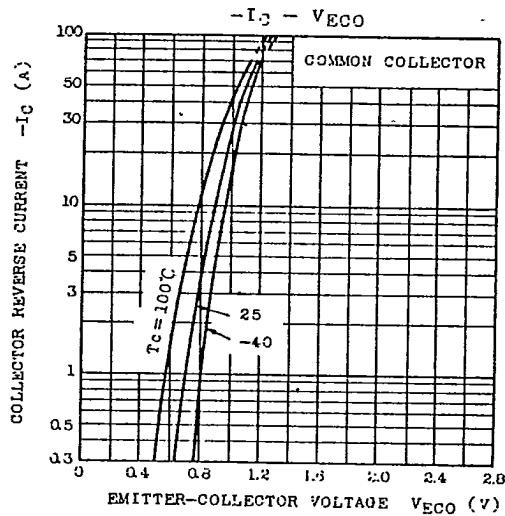
90D 16249 DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

M G 7 5 H 2 C L 1
M G 7 5 H 2 D L 2



TOSHIBA CORPORATION

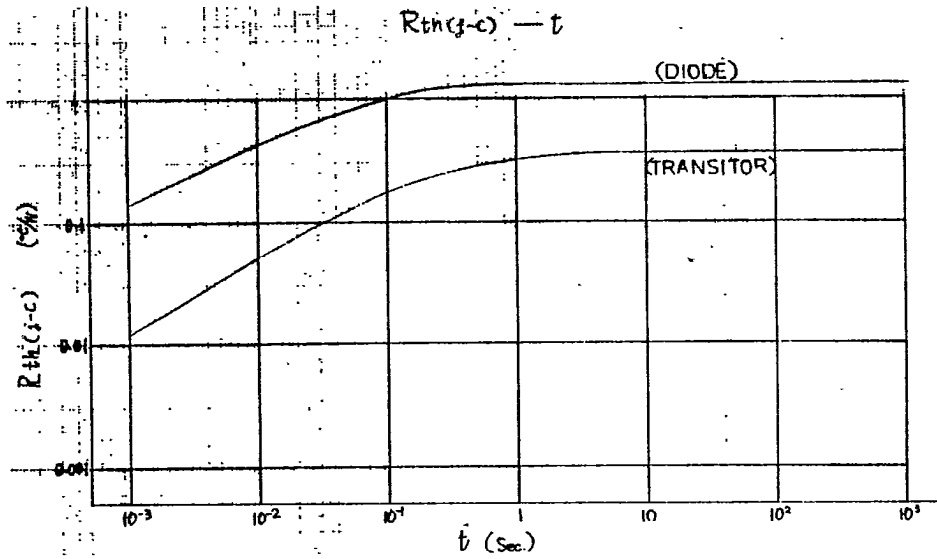
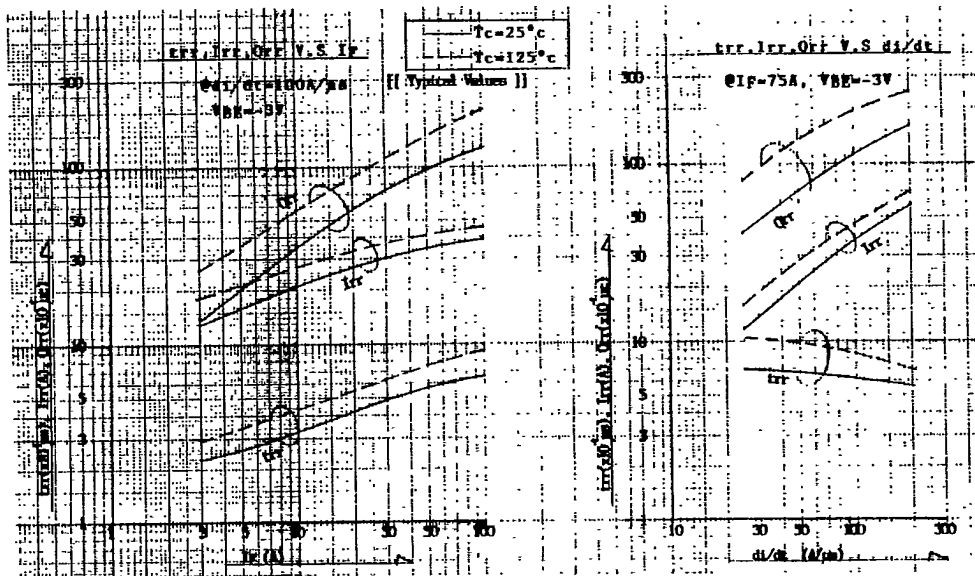
GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)



SEMICONDUCTOR
TECHNICAL DATA

MG75H2CL1
MG75H2DL2



TOSHIBA CORPORATION

GT1A2A